UNIKC Semiconductor

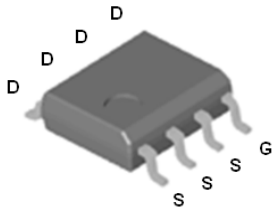
RoHS Compliant

PV551BA

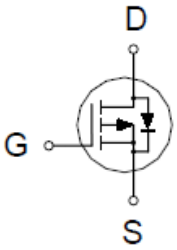
P-Channel Enhancement Mode MOSFET

PRODUCT SUMMARY

$V_{(BR)DSS}$	$R_{DS(ON)}$	I_D
-30V	20mΩ @V_{GS} = -10V	-9A



SOP- 08



ABSOLUTE MAXIMUM RATINGS (T_A = 25 °C Unless Otherwise Noted)

PARAMETERS/TEST CONDITIONS		SYMBOL	LIMITS	UNITS
Drain-Source Voltage		V_{DS}	-30	V
Gate-Source Voltage		V_{GS}	±25	
Continuous Drain Current	T_A = 25 °C	I_D	-9	A
	T_A = 70 °C		-7	
Pulsed Drain Current[1]		I_{DM}	-40	
Avalanche Current		I_{AS}	-23.5	
Avalanche Energy	L=0.1mH	E_{AS}	27	mJ
Power Dissipation[3]	T_A = 25 °C	P_D	3	W
	T_A = 70 °C		2	
Junction & Storage Temperature Range		T_J, T_{STG}	-55 to 150	°C

THERMAL RESISTANCE RATINGS

THERMAL RESISTANCE		SYMBOL	TYPICAL	MAXIMUM	UNITS
Junction-to-Ambient[2]	t ≦10s	$R_{\theta JA}$		40	°C / W
Junction-to-Ambient[2]	Steady-State	$R_{\theta JA}$		72	
Junction-to-Case	Steady-State	$R_{\theta JC}$		30	

[1]Pulse width limited by maximum junction temperature.

[2]The value of $R_{\theta JA}$ is measured with the device mounted on 1in^2 FR-4 board with 2oz.Copper.in a still air environment with T_A=25°C.

[3]The Power dissipation is based on $R_{\theta JA}$ t ≦10s value.

UNIKC Semiconductor

RoHS Compliant

PV551BA

P-Channel Enhancement Mode MOSFET

ELECTRICAL CHARACTERISTICS (T_J = 25 °C, Unless Otherwise Noted)

PARAMETER	SYMBOL	TEST CONDITIONS	LIMITS			UNITS
			MIN	TYP	MAX	
STATIC						
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	V_{GS} = 0V, I_D = -250μA	-30			V
Gate Threshold Voltage	$V_{GS(th)}$	V_{DS} = V_{GS}, I_D = -250μA	-1	-1.5	-3	
Gate-Body Leakage	I_{GSS}	V_{DS} = 0V, V_{GS} = ±25V			±100	nA
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS} = -24V, V_{GS} = 0V			-1	μA
		V_{DS} = -20V, V_{GS} = 0V , T_J = 55 °C			-10	
Drain-Source On-State Resistance[1]	$R_{DS(ON)}$	V_{GS} = -4.5V, I_D = -9A		24	35	mΩ
		V_{GS} = -10V, I_D = -9A		17	20	
Forward Transconductance[1]	g_{fs}	V_{DS} = -5V, I_D = -9A		20		S
DYNAMIC						
Input Capacitance	C_{iss}	V_{GS} = 0V, V_{DS} = -15V, f = 1MHz		1090		pF
Output Capacitance	C_{oss}			150		
Reverse Transfer Capacitance	C_{rss}			120		
Gate Resistance	R_g	V_{GS} = 0V, V_{DS} = 0V, f = 1MHz		8		Ω
Total Gate Charge[2]	Q_g	V_{DS} = -15V I_D = -9A, V_{GS} = -10V		21		nC
Gate-Source Charge[2]	Q_{gs}			2.9		
Gate-Drain Charge[2]	Q_{gd}			6		
Turn-On Delay Time[2]	$t_{d(on)}$	V_{DD} = -15V, I_D ≅ -9A, V_{GS} = -10V,R_{GEN}=6Ω		22		nS
Rise Time[2]	t_r			17		
Turn-Off Delay Time[2]	$t_{d(off)}$			48		
Fall Time[2]	t_f			25		
SOURCE-DRAIN DIODE RATINGS AND CHARACTERISTICS (T_J = 25 °C)						
Continuous Current	I_S				-2.3	A
Forward Voltage[1]	V_{SD}	I_F = -9A, V_{GS} = 0V			-1.3	V
Reverse Recovery Time	t_{rr}	I_F = -9A, dI/dt = 100A / μS		11		nS
Reverse Recovery Charge	Q_{rr}			3		nC

[1]Pulse test : Pulse Width ≤ 300 μsec, Duty Cycle ≤ 2%.

[2]Independent of operating temperature.

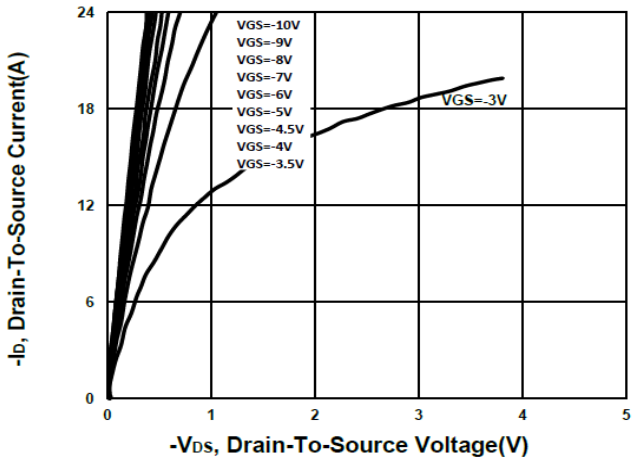
UNIKC Semiconductor

RoHS Compliant

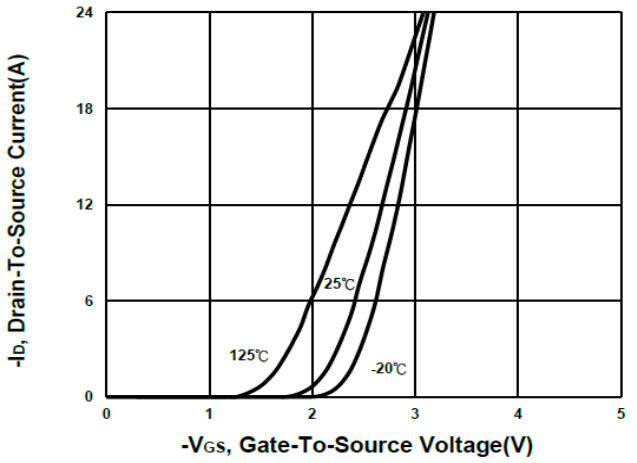
PV551BA

P-Channel Enhancement Mode MOSFET

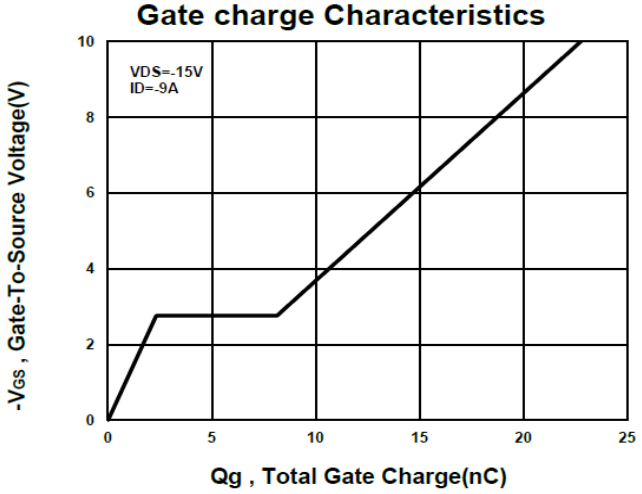
Output Characteristics



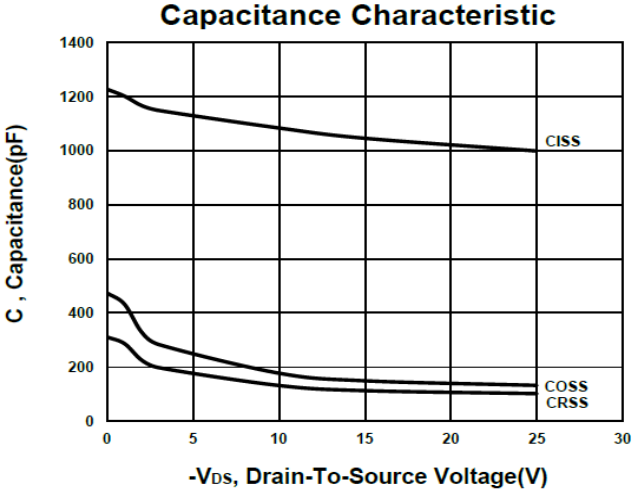
Transfer Characteristics



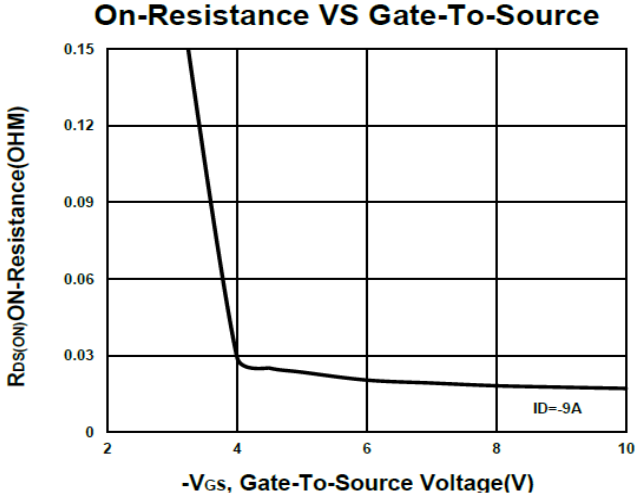
Gate charge Characteristics



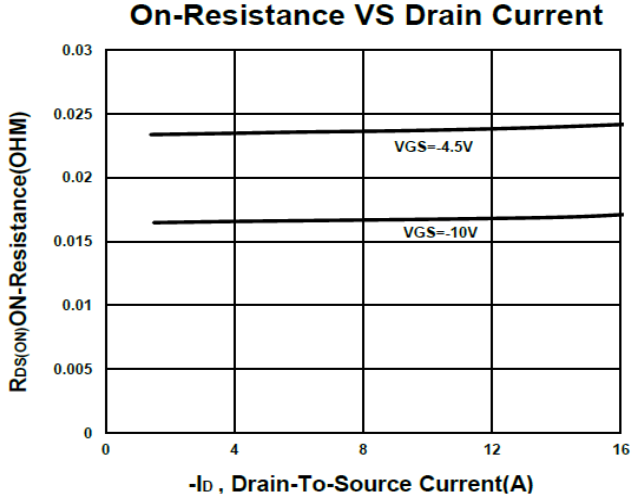
Capacitance Characteristic



On-Resistance VS Gate-To-Source



On-Resistance VS Drain Current



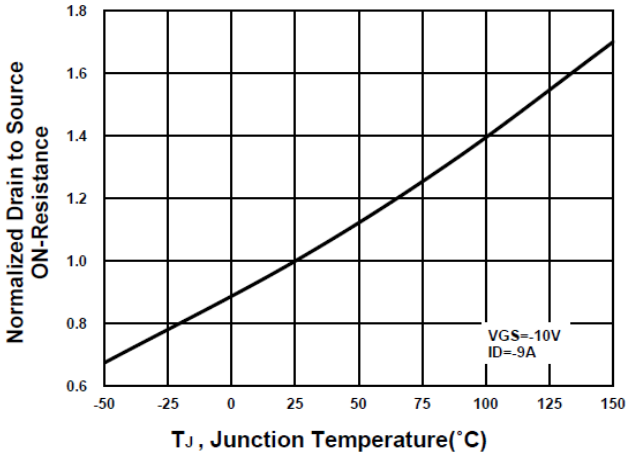
UNIKC Semiconductor

RoHS Compliant

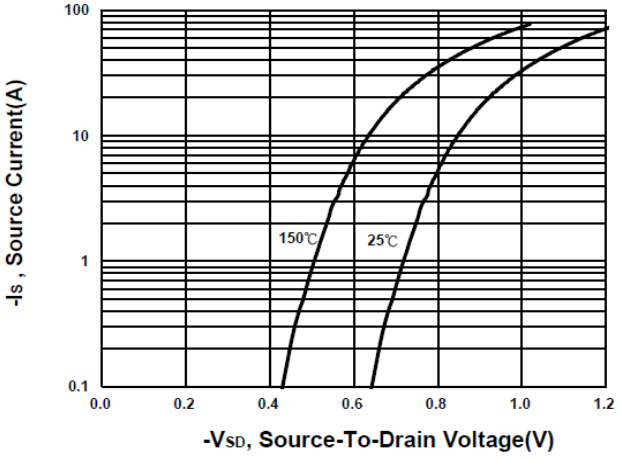
PV551BA

P-Channel Enhancement Mode MOSFET

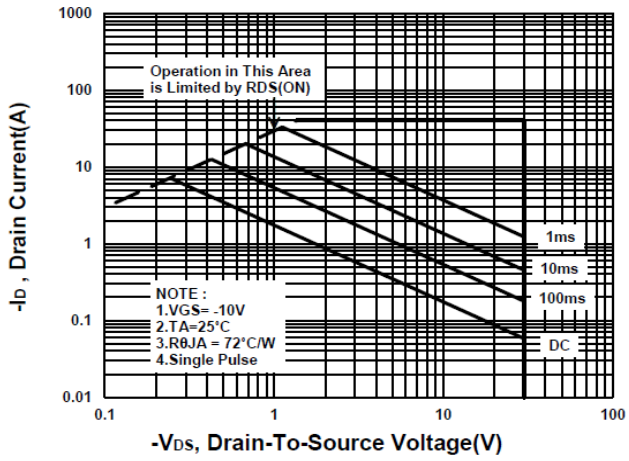
On-Resistance VS Temperature



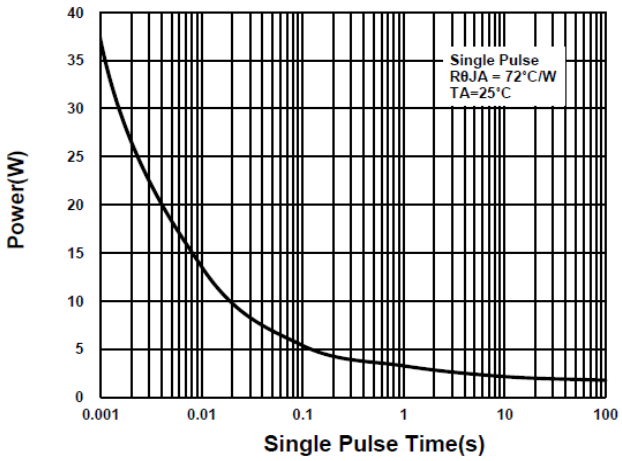
Source-Drain Diode Forward Voltage



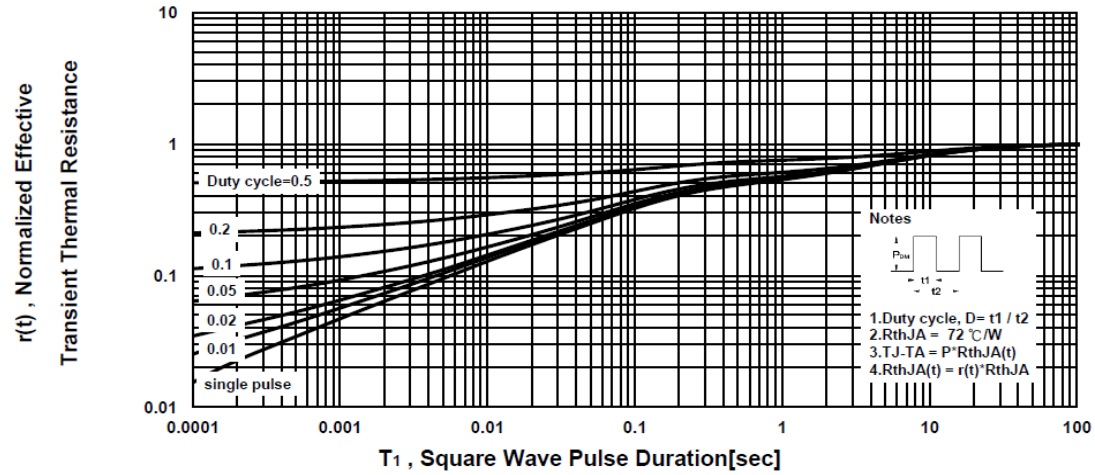
Safe Operating Area



Single Pulse Maximum Power Dissipation



Transient Thermal Response Curve



UNIKC Semiconductor

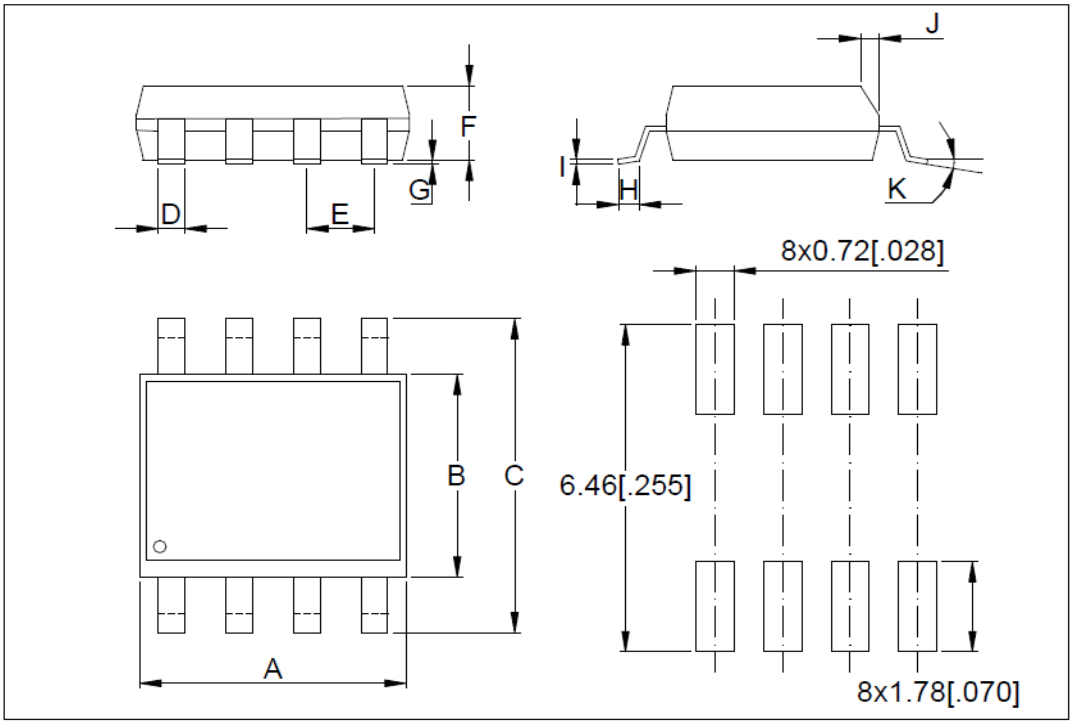
PV551BA

P-Channel Enhancement Mode MOSFET

Package Dimension

SOP-8 MECHANICAL DATA

Dimension	mm			Dimension	mm		
	Min.	Typ.	Max.		Min.	Typ.	Max.
A	4.8	4.9	5.0	H	0.4	0.6	0.93
B	3.8	3.9	4.0	I	0.19	0.21	0.25
C	5.79	6.0	6.2	J	0.25	0.375	0.5
D	0.33	0.4	0.51	K	0°	3°	18°
E	1.25	1.27	1.29				
F	1.1	1.3	1.65				
G	0.05	0.15	0.25				



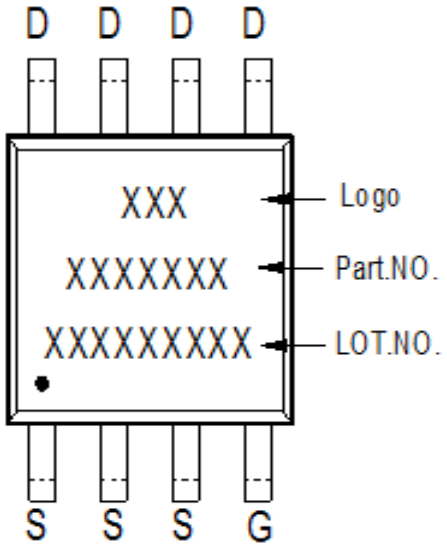
UNIKC Semiconductor

RoHS Compliant

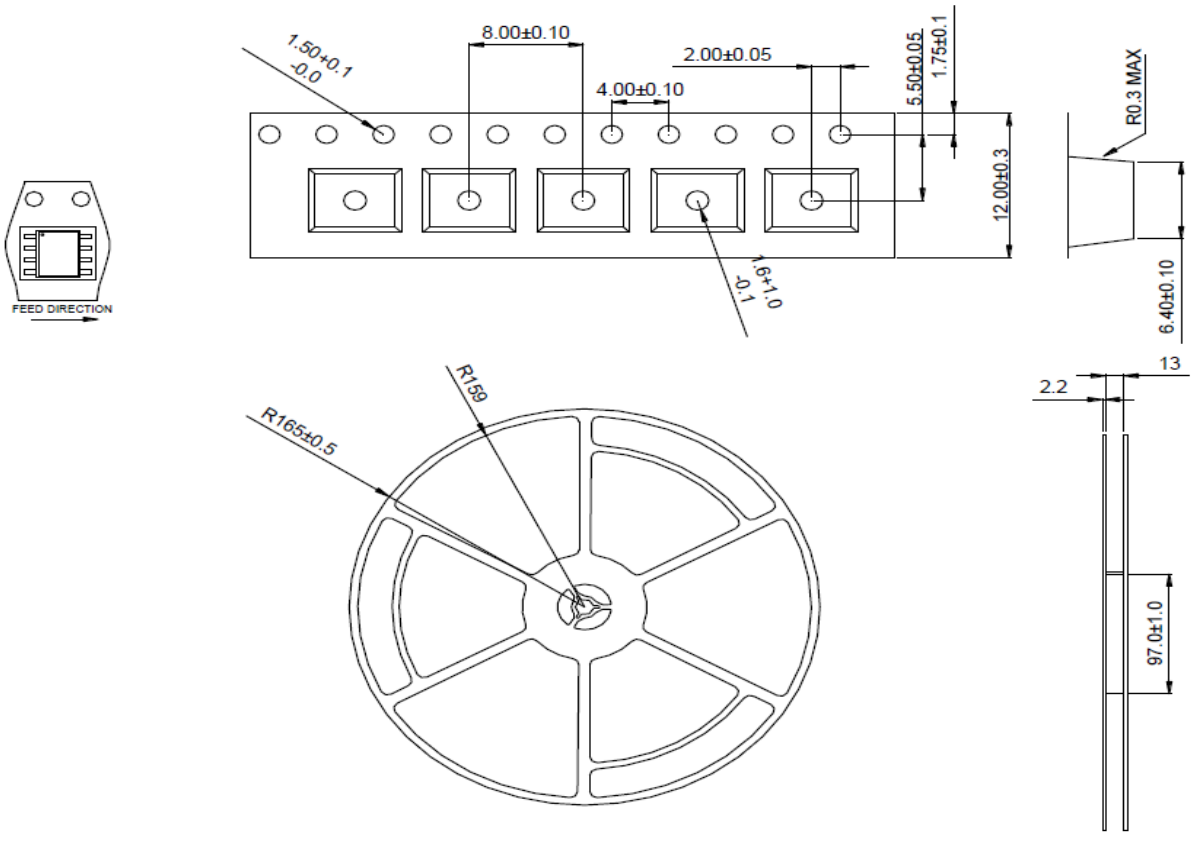
PV551BA

P-Channel Enhancement Mode MOSFET

A. Marking Information



B. Tape&Reel Information:2500pcs/Reel



UNIKC Semiconductor

RoHS Compliant

PV551BA

P-Channel Enhancement Mode MOSFET

C. Lot.No. & Date Code rule

1.LOT.NO.

M N 15M21 03

- 03 → #8~9 Sub-lot No
- 15M21 → Order series no.
- N → Foundry site
- M → Assembly site

2.Date Code

D Y M X XXX

- XXX → Order series no. & Sub-lot No
- X → Week
- M → M : Month (A:Jan , B:Feb , C:Mar ,D :Apr ,E:May ,F:Jun,G:Jul,H:Aug,I:Sep,J:Oct,K:Nov,L:Dec.)
- Y → Y : Year (N : 2011, O : 2012 ...)
- D → Assembly site

3.Date Code (for Small package)

XX Y WW

- WW → Week
- Y → Y : Year (9: 2009,A : 2010, B : 2011 ...)
- XX → Device Name

UNIKC Semiconductor

RoHS Compliant

PV551BA

P-Channel Enhancement Mode MOSFET

D.Label rule

标签内容(Label content)



1	Label Size	30 * 90 mm
2	Font style	Times New Roman or Arial （或可区分英文”O”和数字”0”，”G和”Q”的字型即可）
3	Great Power	Height: 4 mm
4	Package	Height: 2 mm
5	Date	Height: 2 mm Shipping date: YYYY/MM/DD, ex. 2008/09/12
6	Device	Height: 3 mm (Max: 16 Digit)
7	Lot	Height: 3 mm (Max: 9 Digit) Sub lot
8	D/C	Height: 3 mm (Max: 7 Digit)
9	QTY	Height: 3 mm (Max: 6 Digit) Thousand mark is no needed
10	Pb Free label	Pb Diameter: 1 cm bottom color: Green Font color: Black Font style: Arial
11	Halogen Free label	G Diameter: 1 cm bottom color: Green Font color: Black Font style: Arial
12	Scan info	Device / Lot / D/C / QTY , Insert “ / “ between every parts. for example: P3055LDG/G12345601/GGG2301/2000 DPI (Dots per inch): Over 300 dpi Code : Code 128 Height: 6 mm at least